

# **ECE 65: Components & Circuits Lab**

## **Lecture 12**

### **BJT Transfer function**

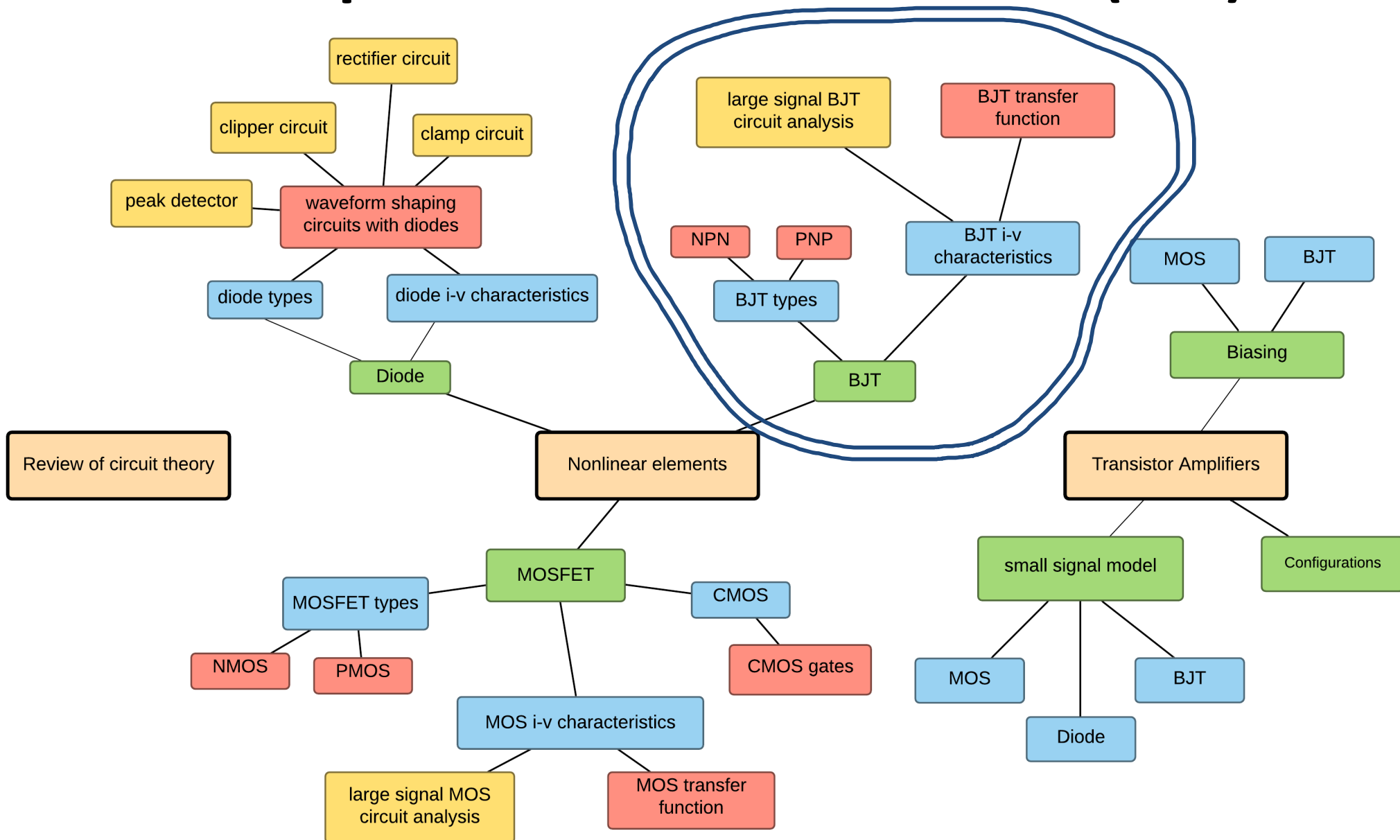
Reference notes: sections 3.2

Sedra & Smith (7<sup>th</sup> Ed): sections 6.1,6.4

Saharnaz Baghdadchi

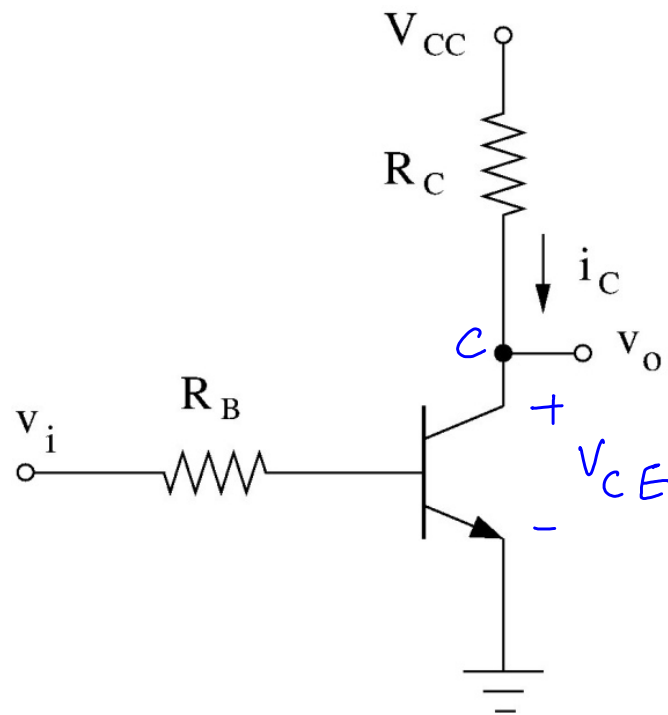
# Course map

## 3. Bipolar Junction Transistor (BJT)



## Discussion question: BJT Transfer Function

how would the output  $v_o = v_{CE}$  change in terms of  $v_i$ ?



# BJT Transfer Function

BE KVL:  $v_i = R_B i_B + v_{BE}$

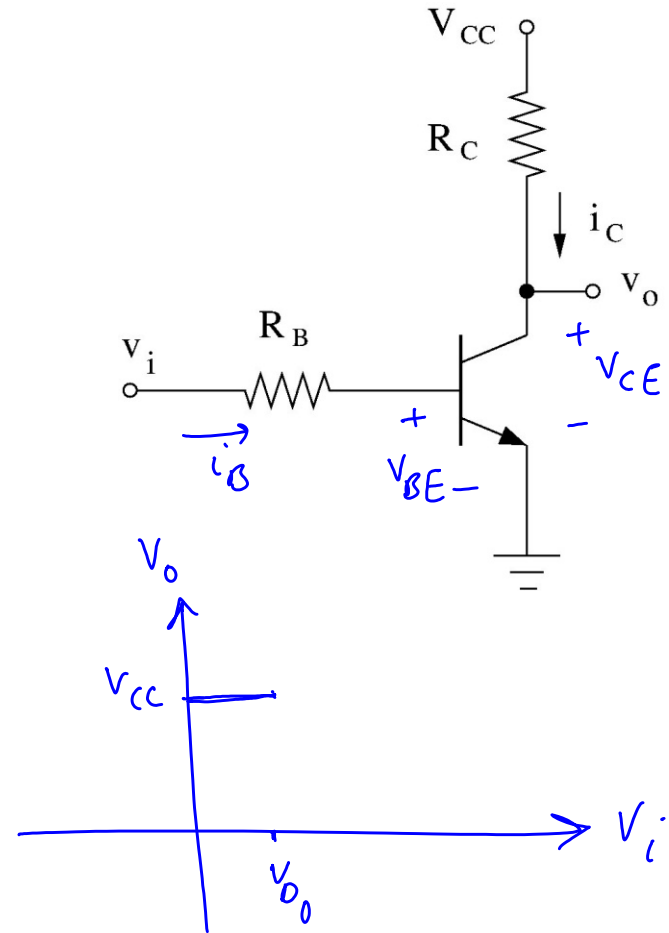
CE KVL:  $V_{CC} = R_C i_C + v_{CE}$

Case 1: BJT is in cut-off

$$i_B = 0, v_{BE} < V_{D0}, i_C = 0, i_E = 0$$

$$v_i = v_{BE} < V_{D0} \rightarrow v_i < V_{D0}$$

$$V_{CC} = R_C \times 0 + v_o \rightarrow v_o = V_{CC}$$



For  $v_i < V_{D0}$ , BJT is in cut-off,  $v_o = V_{CC}$

# BJT Transfer Function

Case 2: BJT is ON,  $V_{DE} = V_{D_0}$

$$i_B = \frac{v_i - V_{BE}}{R_B} = \frac{v_i - V_{D_0}}{R_B},$$

$$V_{CE} = V_{CC} - R_C i_C$$

$$i_C = \beta i_B, \quad V_{CE} \geq V_{D_0}$$

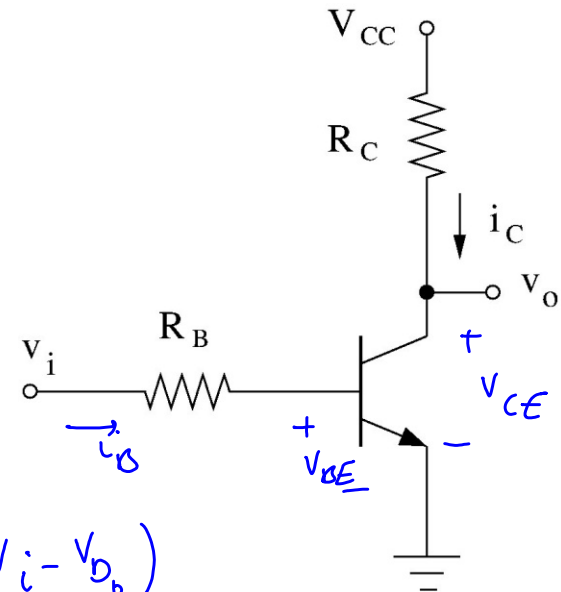
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$$i_C = \frac{\beta}{R_B} (v_i - V_{D_0}), \quad V_{CE} = V_{CC} - \frac{\beta R_C}{R_B} (v_i - V_{D_0})$$

$$V_{CE} \geq V_{D_0} \rightarrow v_i \leq V_{D_0} + \frac{V_{CC} - V_{D_0}}{\beta R_C / R_B}$$

$$v_o = \left( V_{CC} + \frac{\beta R_C}{R_B} V_{D_0} \right) - \frac{\beta R_C}{R_B} v_i$$

For  $v_i \leq V_{D_0} + \frac{V_{CC} - V_{D_0}}{\beta R_C / R_B}$  the BJT is in active mode.



# BJT Transfer Function

Case 3: BJT is in saturation.

$$V_{BE} = V_{D_0}, \quad \boxed{i_c < \beta i_B}, \quad V_{CE} = V_{sat}$$

$$i_B = \frac{V_i - V_{BE}}{R_B},$$

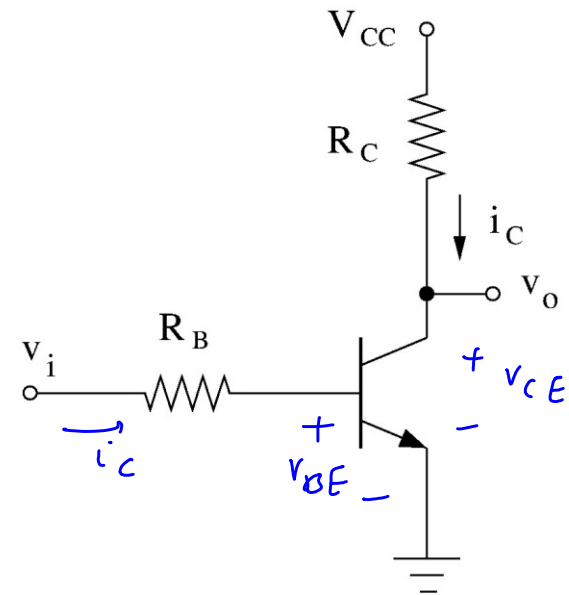
$$V_{CE} = V_{CC} - R_C i_c, \quad i_c = \frac{V_{CC} - V_{sat}}{R_C}$$

$$i_c < \beta i_B \rightarrow \frac{V_{CC} - V_{sat}}{R_C} < \frac{\beta}{R_B} (V_i - V_{D_0})$$

$$V_i > V_{D_0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B}$$

For  $V_i > V_{D_0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B}$ , BJT is in saturation

$$V_o = V_{sat}$$

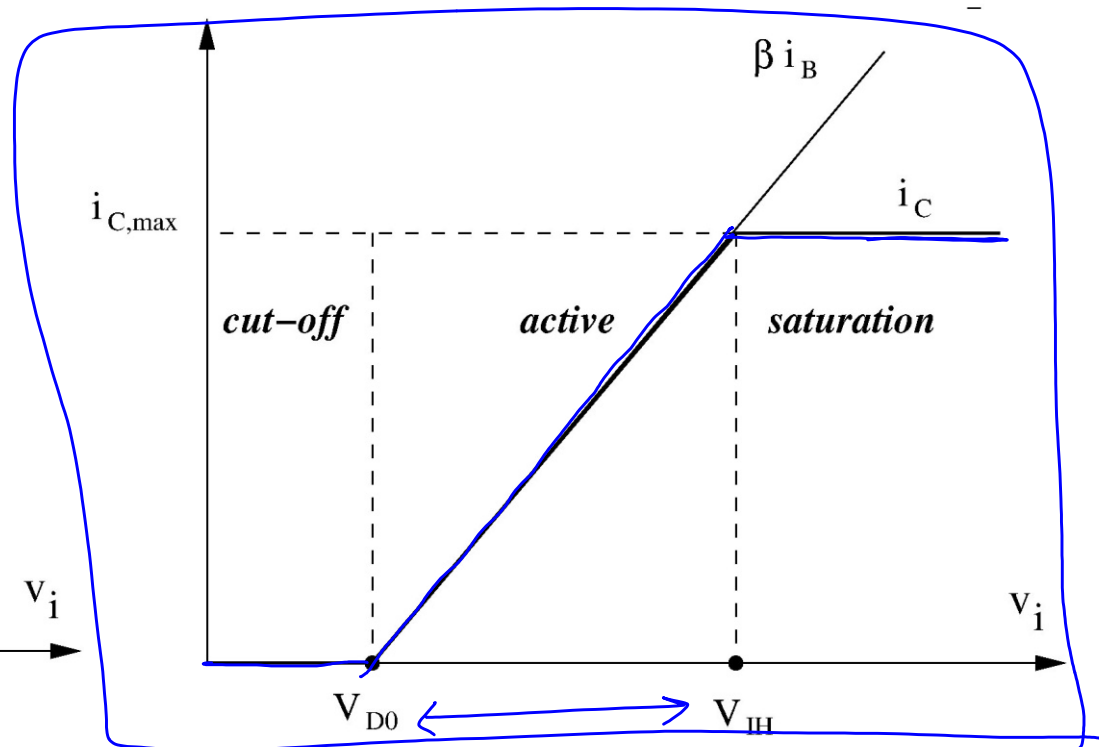
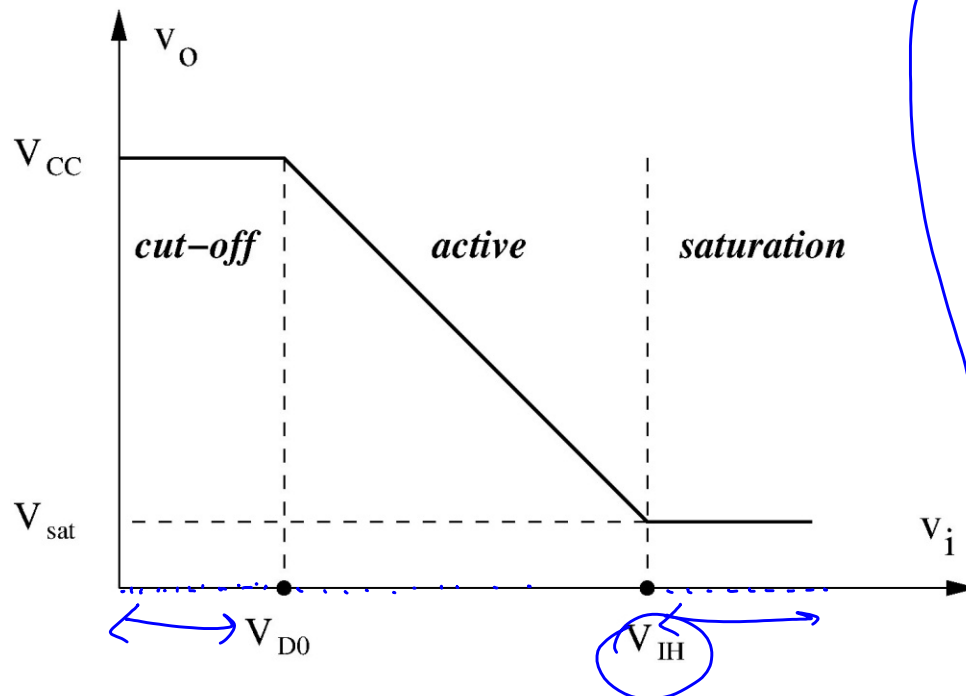
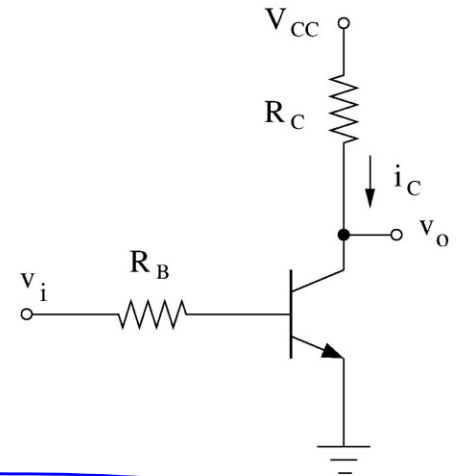


# BJT Transfer Function

$$v_i < V_{D0} \rightarrow \text{BJT in Cutoff}$$

$$V_{D0} \leq v_i \leq V_{D0} + \frac{V_{CC} - V_{D0}}{\beta R_C / R_B} \rightarrow \text{BJT in active}$$

$$V_{D0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B} < v_i \rightarrow \text{BJT in deep saturation}$$



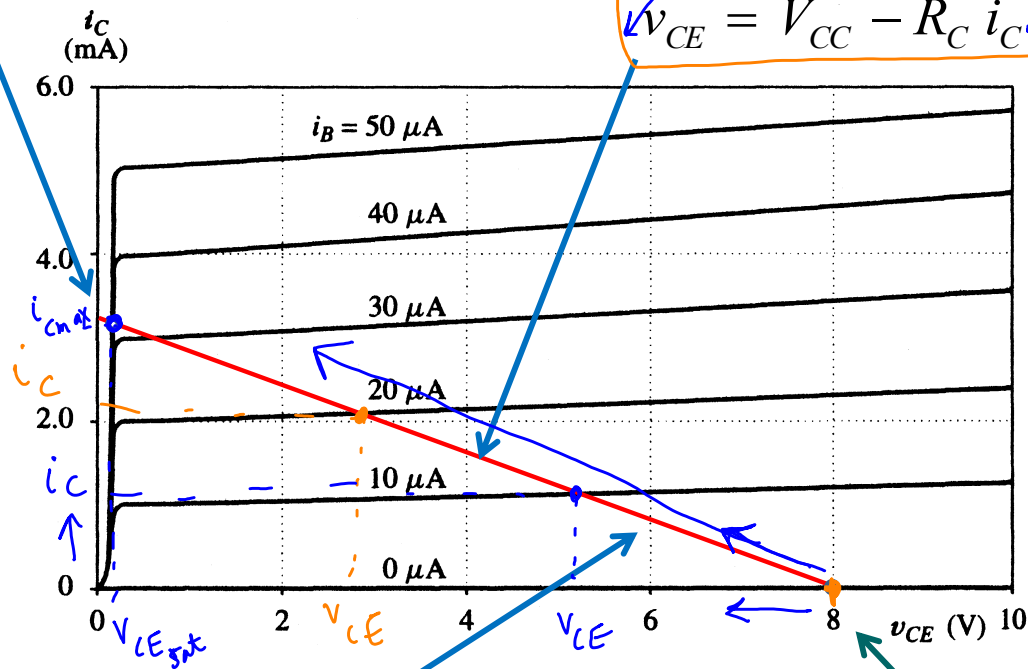
# BJT transfer function on the load line

Saturation :  $V_{IH} < v_i$

$i_B$  increases but  $i_C$  unchanged

Load Line (CE - KVL)

$$v_{CE} = V_{CC} - R_C i_C$$

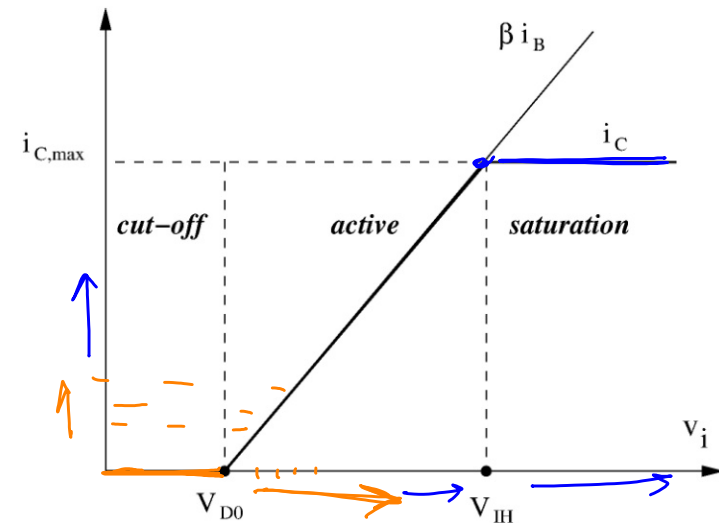
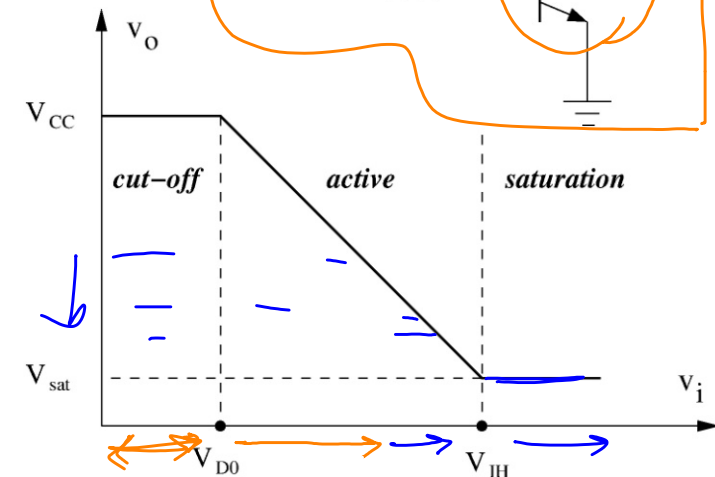
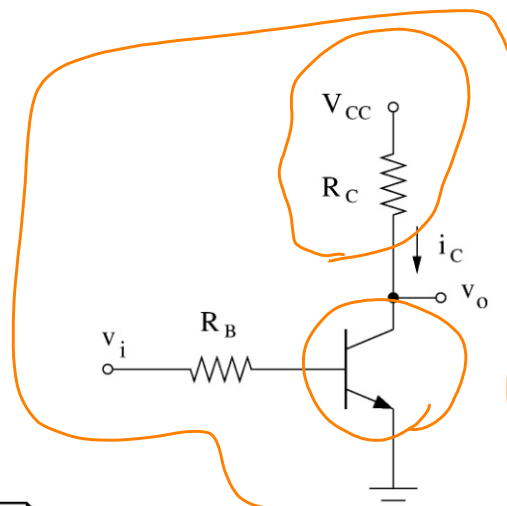


Active :  $V_{D0} \leq v_i \leq V_{IH}$

$i_B$  &  $i_C$  increase together

Cut - off :

$$v_i < V_{D0}$$





# BJT $\beta$ varies substantially

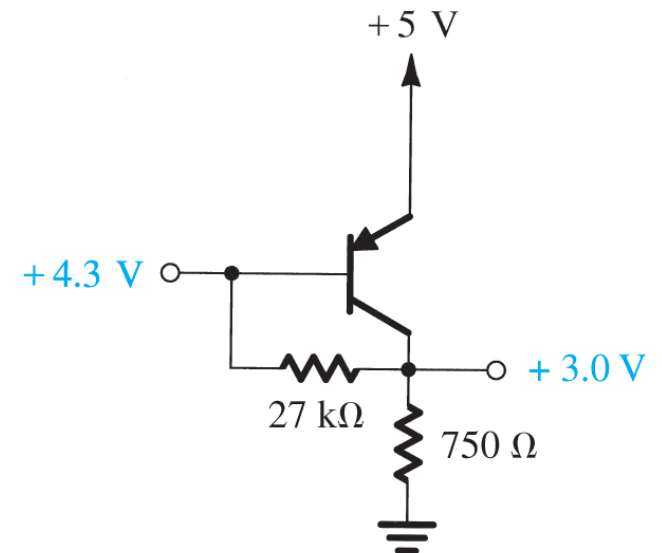
Transistor  $\beta$  depends on many factors:

- Strongly depends on temperature (9% increase per °C)
- Depends on  $i_C$  (not constant as assumed in the model)
- $\beta$  of similarly manufactured BJT can vary (manufacturer spec sheet typically gives a range as well as an average value for  $\beta$ )
- $\beta_{min}$  is an important parameter. For example, to ensure operation in deep saturation for all similar model BJTs, we need to set  $i_C / i_B < \beta_{min}$

## Lecture 12 reading quiz

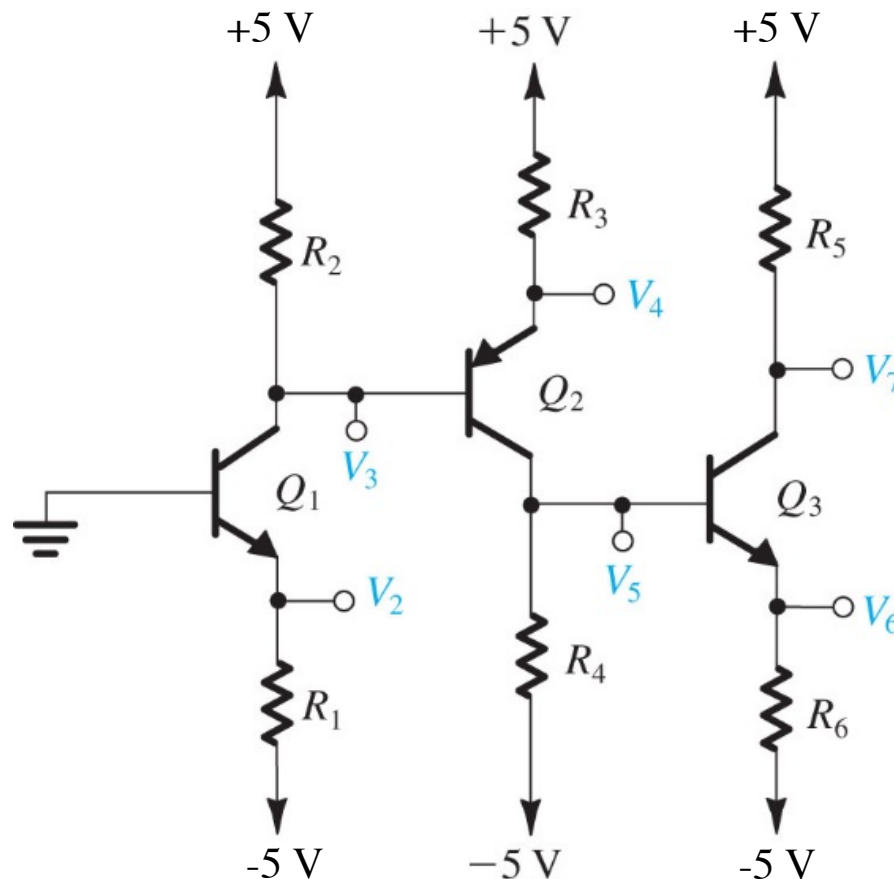
A few measurements on the below circuit produces the labeled voltages.

Find the value of  $\beta$  ( Assume  $V_{D0} = 0.7V$  ).



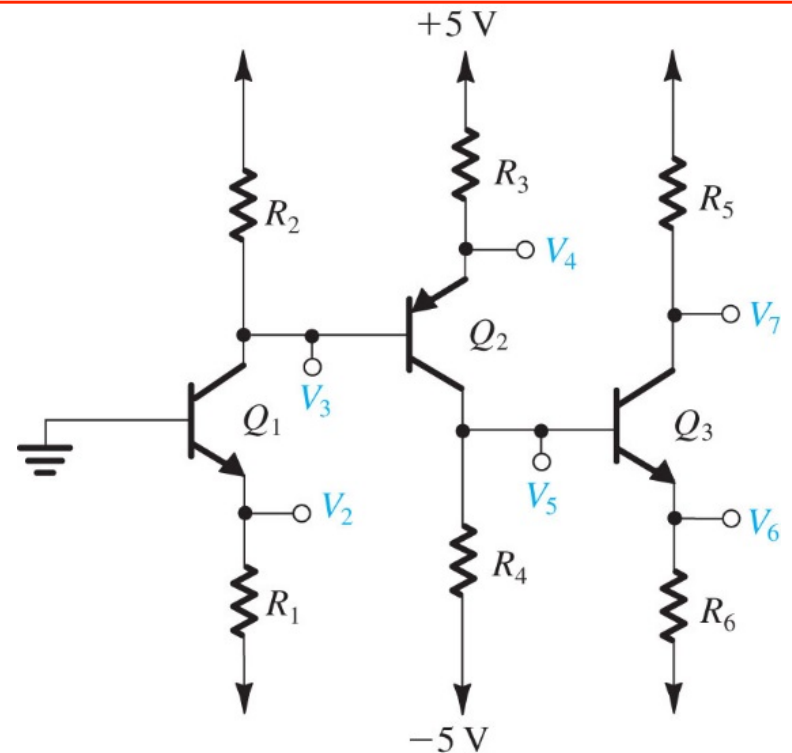
## Discussion question 1.

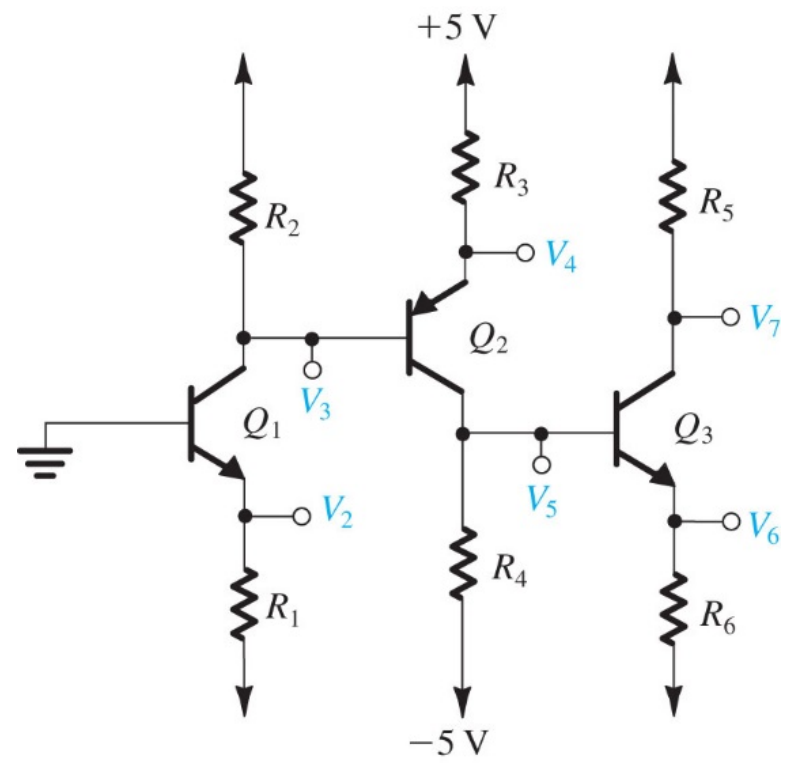
Using  $\beta = \infty$ , design the following circuit so that the transistors operate in the active region and the collector currents in  $Q_1$ ,  $Q_2$ , and  $Q_3$  are 2 mA, 2 mA, and 4 mA, respectively, and  $V_3 = 0$ ,  $V_5 = -4$  V, and  $V_7 = 2$  V.



## Hints:

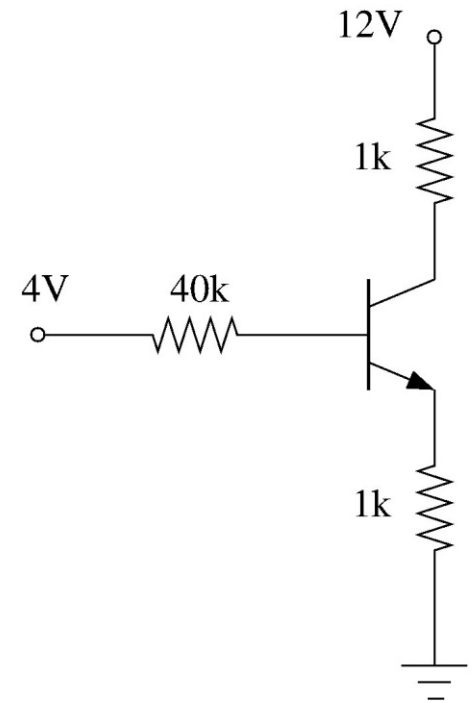
- Assume beta is a very large number such as  $10^6$ . If a BJT is in the active mode with  $I_C = 2\text{mA}$  and  $\beta = 10^6$ , what is  $I_B$ ? What is  $I_B$  approximately equal to?
- Start with  $R_5$  and use Ohm's Law to find the resistor values.
- Remember that all BJTs are ON and in the active mode. Because of this you can use  $V_{BE} = 0.7\text{ V}$  for NPN and  $V_{EB} = 0.7\text{ V}$  for PNP transistors. You can also use the approximate values of  $I_B$  in your equations to find  $I_E$  from  $I_C$  when needed.





## Discussion question 2.

Find the transistor parameters in this BJT circuit. ( $\beta = 100$ ,  $V_{D0} = 0.7V$ ,  $V_{sat} = 0.2 V$ ).



## Hints:

- Write a KVL for the BE loop and check if the BJT is in cut-off. If the BJT is ON, you can use  $V_{BE}=0.7V$ .
- Assume Active mode of operation.
- Write a KVL for the BE loop and another KVL for the CE loop. Also, write relationship between  $I_C$  and  $I_B$  in the active mode and the KCL equation that relates  $I_E$  to  $I_B$  and  $I_C$ .
- Solve the above equations to find all the BJT parameters and verify your assumption.
- You can also start by assuming saturation mode, find the BJT currents and node voltages and check your assumptions.

